

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/612,793	07/02/2003	Arup Bhattacharyya	1303.111US1	5437
21186	7590 03/14/2005		EXAMINER	
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. BOX 2938 MINNEAPOLIS, MN 55402			ERDEM, FAZLI	
			ART UNIT	PAPER NUMBER
			2826	
			DATE MAILED: 03/14/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

Application/Control Number: 10/612,793 Page 2

Art Unit: 2826

DETAILED ACTION

Allowable Subject Matter

1. Claims 1-53 and 72-79 allowed.

2. The following is a statement of reasons for the indication of allowable subject matter:

Regarding Claims 1 and 6, prior art failed to establish a memory cell having first diffusion region connected to bit line, a second diffusion region which store the memory state of the memory cell, a negative differential resistance diode with an intrinsic region between the anode and cathode to assist with stabilizing the memory stat of the memory cell, connected between the second diffusion region and the reference potential line.

Regarding Claims 7-53, prior art failed to establish a p-channel or n-channel access transistor with a first and second p or n-type diffusion region where the second p or n-type diffusion region store the memory state of the memory cell and a negative differential resistance n/i/p or p/i/n diode having n or p-type anode and cathode with an intrinsic region between the anode and cathode to assist with stabilizing the memory state of the memory cell.

Regarding Claims 72-79, prior art failed to establish a memory device with memory array, word lines, bit lines with access transistor with first and second diffusion regions, a negative differential resistance diode with an intrinsic region between the anode and the cathode where the memory cell is used to store charge in the second diffusion region.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

Art Unit: 2826

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

3. Claims 54-71 rejected under 35 U.S.C. 103(a) as being unpatentable over Han (6,611,452) in view of Ashley et al. (5,382,814).

Regarding Claims 54-71, Han discloses reference cells fro TCCT based memory cells where a reference cell produces a voltage rise on a bit line that is proportional rise on a another bit line produced by a TCCT based memory cell in an "on" state. The reference cell includes an NDR device, a gate line device disposed adjacent to the NDR device, a first resistive element coupled between the NDR device and the bit line, and a second resistive element coupled between a sink and the bit line. Han fails to disclose the required intrinsic region requirement. However, Ashley et al. disclose a semiconductor device with low thermally generated leakage current where in columns 6 and 7, the required intrinsic region is disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required intrinsic region configuration in Han as taught by Ashely et al. in order to have a memory cell with higher performance.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.

Application/Control Number: 10/612,793

Art Unit: 2826

Page 4

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE March 6, 2005

NATHAN J. FLYMAN SUPERVISORY PATENT ELERANDER TECHNOLOGY CENTER 28 10